In the Claims

Claims 1-4 (Canceled).

5. (Currently amended) A method of forming an electrical connection comprising:

forming a diffusion region in semiconductive material, the diffusion region having an outer surface;

forming a conductive line laterally spaced from the semiconductive material and diffusion region, a predominate portion of the conductive line being disposed elevationally below the diffusion region outer surface; ~~and~~

interconnecting the conductive line and the diffusion region with electrically conductive material; and

wherein an entirety of the conductive line is laterally spaced from the semiconductive material.

6. (Original) The method of claim 5, wherein the interconnecting the conductive line and the diffusion region comprises forming the electrically conductive material over both the conductive line and the diffusion region.

7. (Original) The method of claim 5, wherein the forming of the conductive line comprises:

forming an isolation oxide region laterally adjacent the semiconductive material, the oxide region having a lateral width;

removing a portion of the isolation oxide intermediate the lateral width; and

replacing at least some of the removed isolation oxide with electrically conductive material.

8. (Original) The method of claim 5, wherein the forming of the conductive line comprises:

forming an isolation oxide region laterally adjacent the semiconductive material, the oxide region having a lateral width;

removing a portion of the isolation oxide intermediate the lateral width and to a greater degree in an elevationally downward direction than a laterally outward direction; and

replacing at least some of the removed isolation oxide with electrically conductive material.

9. (Original) The method of claim 5, wherein the forming of the conductive line comprises:

forming an isolation oxide region laterally adjacent the semiconductive material, the oxide region having a first lateral width;

removing a portion of the isolation oxide at least intermediate the lateral width;

forming oxide material within the first lateral width and to a degree sufficient to occupy less than the first lateral width and to define a second lateral width; and

replacing at least some of the removed isolation oxide with electrically conductive material.

Claims 10-39 (Canceled).

40. (Currently amended) A method of forming an electrical connection comprising:

forming a conductive node in semiconductive material;

forming a conductive line laterally spaced from the semiconductive material and conductive node, a predominate portion of the conductive line being disposed elevationally below the conductive node; ~~and~~

interconnecting the conductive line and the conductive node with electrically conductive material; and

wherein the conductive node comprises an uppermost surface, and wherein the conductive line comprises an uppermost surface which is coplanar with the uppermost surface of the conductive node.

41. (Previously presented) The method of claim 40, wherein the forming of the conductive node comprises forming a source/drain region.

42. (Previously presented) The method of claim 40, wherein the interconnecting of the conductive line and the conductive node comprises forming the electrically conductive material over both the conductive line and the conductive node.

43. (Previously presented) The method of claim 40, wherein the forming of the conductive line and the electrically conductive material comprises forming both from the same material.

44. (Previously presented) The method of claim 40, wherein the forming of the conductive line and the electrically conductive material comprises forming both from different material.

45. (Previously presented) The method of claim 40 further comprising forming insulating material between the conductive line and the conductive node.

46. (Previously presented) The method of claim 40 further comprising forming insulating material between the conductive line and the semiconductive material.

47. (Previously presented) The method of claim 40 further comprising forming oxide material between the conductive line and the semiconductive material.

48. (Previously presented) The method of claim 40, wherein the forming of the conductive line and the electrically conductive material comprises forming both from undoped polysilicon, and further comprising implanting dopants into the undoped polysilicon.

49. (Previously presented) The method of claim 40, wherein the forming of the conductive line and the electrically conductive material comprises forming both from doped polysilicon.

50. (Previously presented) The method of claim 40, wherein the forming of the conductive line and the electrically conductive material comprises forming both from refractory metals.

51. (Previously presented) The method of claim 40, wherein the forming of the conductive line comprises:

forming an isolation oxide region laterally adjacent the semiconductive material, the oxide region having a lateral width;

removing a portion of the isolation oxide intermediate the lateral width; and

replacing at least some of the removed isolation oxide with electrically conductive material.

52. (Previously presented) The method of claim 40, wherein the forming of the conductive line comprises:

forming an isolation oxide region laterally adjacent the semiconductive material, the oxide region having a lateral width;

removing a portion of the isolation oxide intermediate the lateral width and to a greater degree in an elevationally downward direction than a laterally outward direction; and

replacing at least some of the removed isolation oxide with electrically conductive material.

53. (Previously presented) The method of claim 40, wherein the forming of the conductive line comprises:

forming an isolation oxide region laterally adjacent the semiconductive material, the oxide region having a first lateral width;

removing a portion of the isolation oxide at least intermediate the lateral width;

forming oxide material within the first lateral width and to a degree sufficient to occupy less than the first lateral width and to define a second lateral width; and

replacing at least some of the removed isolation oxide with electrically conductive material.

Claim 54 (Canceled).

55. (Previously presented) The method of claim 5, wherein the outer surface of the diffusion region comprises an uppermost surface, and wherein the conductive line comprises an uppermost surface which is coplanar with the uppermost surface of the diffusion region.

56. (Previously presented) The method of claim 6, wherein the forming of the electrically conductive material over both the conductive line and the diffusion region occurs after completing the forming of the diffusion region.

57. (Previously presented) The method of claim 40, wherein an entirety of the conductive line is laterally spaced from the semiconductive material.

Claim 58 (Canceled).

59. (Previously presented) The method of claim 42, wherein the forming of the electrically conductive material over both the conductive line and the conductive node occurs after completing the forming of the conductive node.

60. (New) A method of forming an electrical connection comprising:

forming a diffusion region in semiconductive material, the diffusion region having an outer surface;

forming a conductive line laterally spaced from the semiconductive material and diffusion region, a predominate portion of the conductive line being disposed elevationally below the diffusion region outer surface;

interconnecting the conductive line and the diffusion region with electrically conductive material; and

wherein the outer surface of the diffusion region comprises an uppermost surface, and wherein the conductive line comprises an uppermost surface which is coplanar with the uppermost surface of the diffusion region.

61. (New) A method of forming an electrical connection comprising:

forming a diffusion region in semiconductive material, the diffusion region having an outer surface;

forming a conductive line laterally spaced from the semiconductive material and diffusion region, a predominate portion of the conductive line being disposed elevationally below the diffusion region outer surface;

interconnecting the conductive line and the diffusion region with electrically conductive material;

wherein the interconnecting the conductive line and the diffusion region comprises forming the electrically conductive material over both the conductive line and the diffusion region; and

wherein the forming of the electrically conductive material over both the conductive line and the diffusion region occurs after completing the forming of the diffusion region.

62. (New) A method of forming an electrical connection comprising:

forming a conductive node in semiconductive material;

forming a conductive line laterally spaced from the semiconductive material and conductive node, a predominate portion of the conductive line being disposed elevationally below the conductive node;

interconnecting the conductive line and the conductive node with electrically conductive material; and

wherein an entirety of the conductive line is laterally spaced from the semiconductive material.

63. (New) A method of forming an electrical connection comprising:

forming a conductive node in semiconductive material;

forming a conductive line laterally spaced from the semiconductive material and conductive node, a predominate portion of the conductive line being disposed elevationally below the conductive node;

interconnecting the conductive line and the conductive node with electrically conductive material;

wherein the interconnecting of the conductive line and the conductive node comprises forming the electrically conductive material over both the conductive line and the conductive node; and

wherein the forming of the electrically conductive material over both the conductive line and the conductive node occurs after completing the forming of the conductive node.